Complementary Plastic Power Transistors

NPN/PNP Silicon DPAK For Surface Mount Applications

MJD200 (NPN), MJD210 (PNP)

Designed for low voltage, low-power, high-gain audio amplifier applications.

Features

- High DC Current Gain
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Low Collector-Emitter Saturation Voltage
- High Current-Gain Bandwidth Product
- Annular Construction for Low Leakage
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit	
Collector-Base Voltage	V _{CB}	40	Vdc	
Collector-Emitter Voltage	V _{CEO}	25	Vdc	
Emitter-Base Voltage	V _{EB}	8.0	Vdc	
Collector Current – Continuous	Ι _C	5.0	Adc	
Collector Current – Peak	I _{CM}	10	Adc	
Base Current	I _B	1.0	Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	12.5 0.1	W W/°C	
Total Power Dissipation (Note 1) @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	1.4 0.011	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C	
ESD – Human Body Model	HBM	3B	V	
ESD – Machine Model	MM	С	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

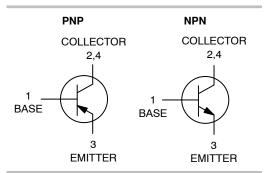
1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.



ON Semiconductor®

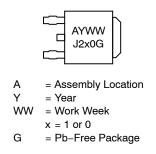
www.onsemi.com

SILICON POWER TRANSISTORS 5 AMPERES 25 VOLTS, 12.5 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ ext{ heta}JC}$	10	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

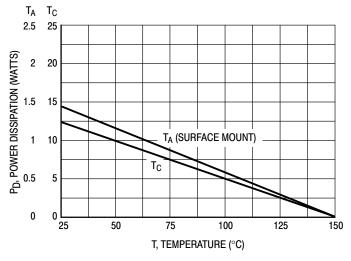
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

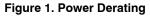
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	25	-	Vdc
Collector Cutoff Current ($V_{CB} = 40 \text{ Vdc}, I_E = 0$) ($V_{CB} = 40 \text{ Vdc}, I_E = 0, T_J = 125^{\circ}C$)	I _{CBO}		100 100	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 8 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	100	nAdc
ON CHARACTERISTICS				
C Current Gain (Note 3), (I _C = 500 mAdc, V _{CE} = 1 Vdc) (I _C = 2 Adc, V _{CE} = 1 Vdc) (I _C = 5 Adc, V _{CE} = 2 Vdc)	h _{FE}	70 45 10	_ 180 _	_
Collector-Emitter Saturation Voltage (Note 3) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 2 \text{ Adc}$, $I_B = 200 \text{ mAdc}$) ($I_C = 5 \text{ Adc}$, $I_B = 1 \text{ Adc}$)	V _{CE(sat)}	- - -	0.3 0.75 1.8	Vdc
Base-Emitter Saturation Voltage (Note 3) ($I_c = 5 \text{ Adc}, I_B = 1 \text{ Adc}$)	V _{BE(sat)}	-	2.5	Vdc
Base-Emitter On Voltage (Note 3) (I _C = 2 Adc, V _{CE} = 1 Vdc)	V _{BE(on)}	-	1.6	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (Note 4) (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)	f _T	65	-	MHz
Output Capacitance (Vcp = 10 Vdc μ = 0 f = 0 1 MHz)	C _{ob}			pF

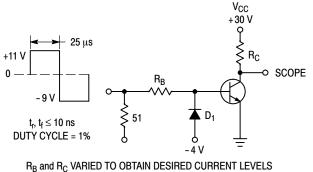
(V_{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz) MJD200 MJD210, NJVMJD210T4G

3. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \approx 2%.

4. $f_T = |h_{fe}| \bullet f_{test}$.

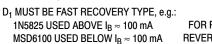


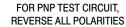


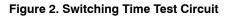


80

120







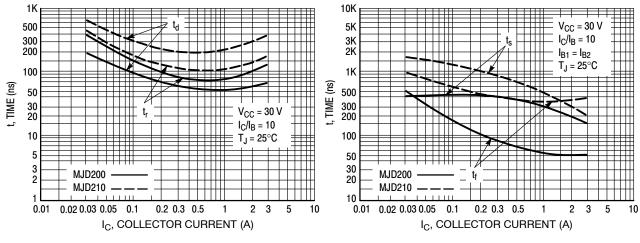
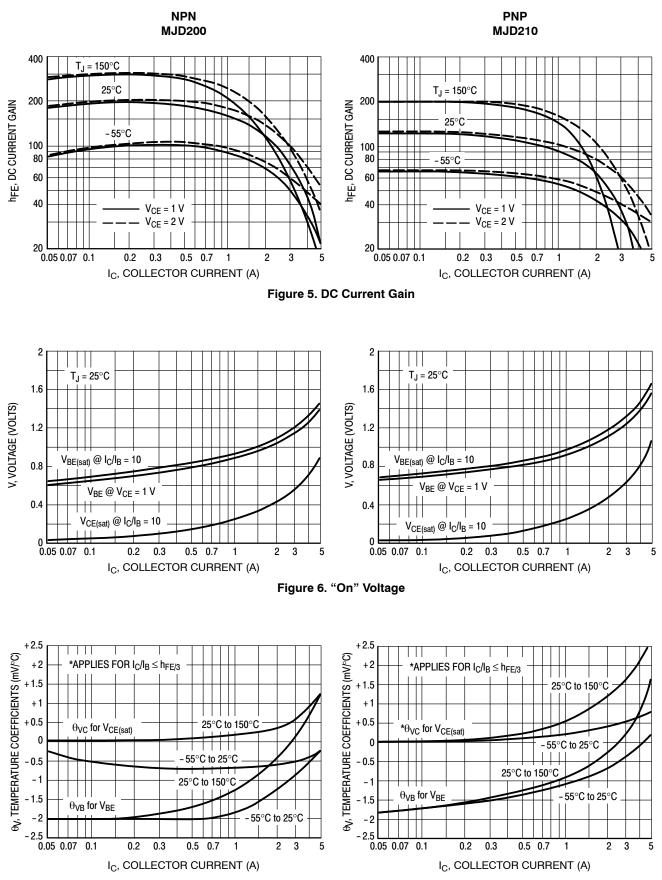


Figure 3. Turn-On Time

Figure 4. Turn-Off Time





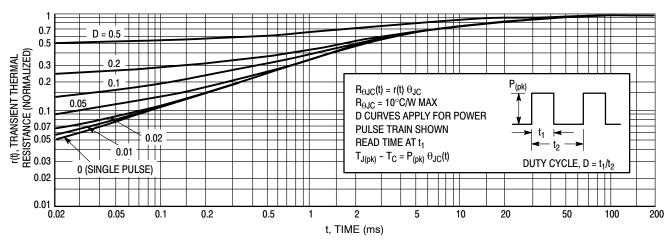


Figure 8. Thermal Response

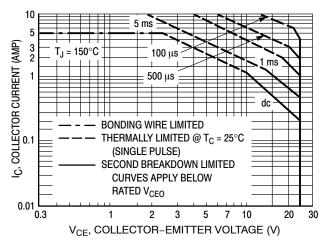
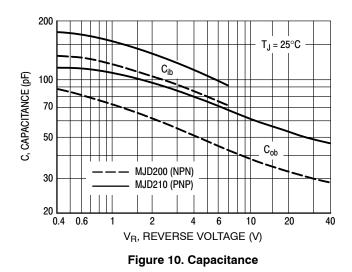


Figure 9. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



ORDERING INFORMATION

Device	Package Type	Shipping [†]	
MJD200G	DPAK (Pb–Free)	75 Units / Rail	
MJD200RLG	DPAK (Pb-Free)	1,800 / Tape & Reel	
MJD200T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	
MJD210G	DPAK (Pb-Free)	75 Units / Rail	
MJD210RLG	DPAK (Pb-Free)	1,800 / Tape & Reel	
MJD210T4G	DPAK (Pb-Free)	2,500 / Tape & Reel	
NJVMJD210T4G*	DPAK (Pb-Free)	2,500 / Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable





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